

# Bo Song

## List of Publications by Year in descending order

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34  
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1,715  
citations

516215

16  
h-index

642321

23  
g-index

34  
all docs

34  
docs citations

34  
times ranked

2226  
citing authors

#	ARTICLE	IF	CITATIONS
1	Esaki Diodes in van der Waals Heterojunctions with Broken-Gap Energy Band Alignment. Nano Letters, 2015, 15, 5791-5798.	4.5	319
2	InAlN/AlN/GaN HEMTs With Regrown Ohmic Contacts and $f_{T}$ of 370 GHz. IEEE Electron Device Letters, 2012, 33, 988-990.	2.2	292
3	1.9-kV AlGaIn/GaN Lateral Schottky Barrier Diodes on Silicon. IEEE Electron Device Letters, 2015, 36, 375-377.	2.2	160
4	1.7-kV and $0.55 \times 10^{12} \text{ cm}^{-2}$ GaN p-n Diodes on Bulk GaN Substrates With Avalanche Capability. IEEE Electron Device Letters, 2016, 37, 161-164.	2.2	153
5	Near unity ideality factor and Shockley-Read-Hall lifetime in GaN-on-GaN p-n diodes with avalanche breakdown. Applied Physics Letters, 2015, 107, .	1.5	146
6	Gate-recessed integrated E/D GaN HEMT technology with $f_{T}/f_{max} > 300$ GHz. IEEE Electron Device Letters, 2013, 34, 741-743.	2.2	94
7	Ultrascaled InAlN/GaN High Electron Mobility Transistors with Cutoff Frequency of 400 GHz. Japanese Journal of Applied Physics, 2013, 52, 08JN14.	0.8	66
8	Quaternary Barrier InAlGaIn HEMTs With $f_{T}/f_{max}$ of 230/300 GHz. IEEE Electron Device Letters, 2013, 34, 378-380.	2.2	58
9	Polarization-Induced GaN-on-Insulator E/D Mode p-Channel Heterostructure FETs. IEEE Electron Device Letters, 2013, 34, 852-854.	2.2	55
10	High breakdown single-crystal GaN p-n diodes by molecular beam epitaxy. Applied Physics Letters, 2015, 107, .	1.5	53
11	Strained GaN quantum-well FETs on single crystal bulk AlN substrates. Applied Physics Letters, 2017, 110, .	1.5	48
12	High Holding Voltage SCR-LDMOS Stacking Structure With Ring-Resistance-Triggered Technique. IEEE Electron Device Letters, 2013, 34, 1178-1180.	2.2	47
13	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. Applied Physics Letters, 2014, 104, .	1.5	42
14	Ultralow-Leakage AlGaIn/GaN High Electron Mobility Transistors on Si With Non-Alloyed Regrown Ohmic Contacts. IEEE Electron Device Letters, 2016, 37, 16-19.	2.2	37
15	Effect of Fringing Capacitances on the RF Performance of GaN HEMTs With T-Gates. IEEE Transactions on Electron Devices, 2014, 61, 747-754.	1.6	34
16	Impact of $\text{CF}_4$ plasma treatment on threshold voltage and mobility in $\text{Al}_2\text{O}_3/\text{InAlN}/\text{GaN}$ MOSHEMTs. Applied Physics Express, 2014, 7, 031002.	1.1	19
17	Dual optical marker Raman characterization of strained GaN-channels on AlN using AlN/GaN/AlN quantum wells and $^{15}\text{N}$ isotopes. Applied Physics Letters, 2015, 106, .	1.5	13
18	Steep Sub-Boltzmann Switching in AlGaIn/GaN Phase-FETs With ALD $\text{VO}_2$ . IEEE Transactions on Electron Devices, 2018, 65, 945-949.	1.6	13

#	ARTICLE	IF	CITATIONS
19	Electron mobility in polarization-doped Al <sub>0.2</sub> GaN with a low concentration near 10 <sup>17</sup> cm <sup>-3</sup> . Applied Physics Letters, 2017, 110, 182102.	1.5	11
20	AlGa <sub>N</sub> /Ga <sub>N</sub> HEMTs on Si by MBE with regrown contacts and $f_{T,max} = 153$ GHz. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 887-889.	0.8	10
21	A Novel Capacitance-Coupling-Triggered SCR for Low-Voltage ESD Protection Applications. IEEE Electron Device Letters, 2010, 31, 1089-1091.	2.2	9
22	Unique opportunity to harness polarization in GaN to override the conventional power electronics figure-of-merits. , 2015, , .		7
23	Compact MOS-triggered SCR with faster turn-on speed for ESD protection. Microelectronics Reliability, 2010, 50, 1393-1397.	0.9	6
24	Monolithically integrated E/D-mode InAlN HEMTs with $f_{T,max} = 200/220$ GHz. , 2012, , .		6
25	Trigger voltage walk-in effect of ESD protection device in HVCMOS. , 2010, , .		3
26	High-voltage polarization-induced vertical heterostructure p-n junction diodes on bulk GaN substrates. , 2015, , .		3
27	Distributed polarization-doped GaN p <sup>+</sup> n diodes with near-unity ideality factor and avalanche breakdown voltage of 1.25 kV. Applied Physics Letters, 2022, 120, .	1.5	3
28	GaN lateral PolarSJs: Polarization-doped super junctions. , 2014, , .		2
29	Comparing buffer leakage in PolarMOSH on SiC and free-standing GaN substrates. , 2016, , .		2
30	Comparison of different MOS-triggered SCR structures for on-chip ESD protection. , 2011, , .		1
31	THz devices based on 2D electron systems. , 2015, , .		1
32	Vertical Ga <sub>0.2</sub> O <sub>0.3</sub> Schottky barrier diodes on single-crystal $\beta$ -Ga <sub>0.2</sub> O <sub>0.3</sub> ( $\lambda = 201$ ) substrates. , 2016, , .		1
33	Investigation of forward transient characteristics of vertical GaN-on-GaN p-n diodes. , 2016, , .		1
34	Investigation of problems in JEDEC HBM ESD test standard. , 2008, , .		0